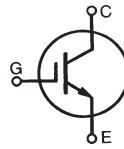


# GenX3™ 600V IGBT

Ultra Low V<sub>sat</sub> PT IGBT for up to 5kHz switching

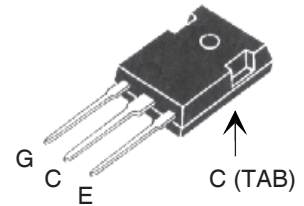
## IXGH72N60A3 IXGT72N60A3



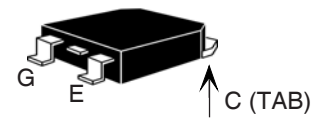
**V<sub>CES</sub> = 600V**  
**I<sub>C110</sub> = 72A**  
**V<sub>CE(sat)</sub> ≤ 1.35V**  
**t<sub>fi(typ)</sub> = 250ns**

Symbol	Test Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>C</sub> = 25°C to 150°C	600	V
V <sub>CGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GE</sub> = 1MΩ	600	V
V <sub>GES</sub>	Continuous	± 20	V
V <sub>GEM</sub>	Transient	± 30	V
I <sub>C25</sub>	T <sub>C</sub> = 25°C (limited by leads)	75	A
I <sub>C110</sub>	T <sub>C</sub> = 110°C	72	A
I <sub>CM</sub>	T <sub>C</sub> = 25°C, 1ms	400	A
<b>SSOA</b> <b>(RBSOA)</b>	V <sub>GE</sub> = 15V, T <sub>VJ</sub> = 125°C, R <sub>G</sub> = 3Ω Clamped inductive load @ ≤ 600V	I <sub>CM</sub> = 150	A
P <sub>C</sub>	T <sub>C</sub> = 25°C	540	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6mm (0.062 in.) from case for 10s	300	°C
T <sub>SOLD</sub>	Plastic body for 10 seconds	260	°C
M <sub>d</sub>	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

### TO-247 (IXGH)



### TO-268 (IXGT)



G = Gate      C = Collector  
E = Emitter    TAB = Collector

### Features

- Optimized for low conduction losses
- Square RBSOA
- International standard packages

### Advantages

- High power density
- Low gate drive requirement

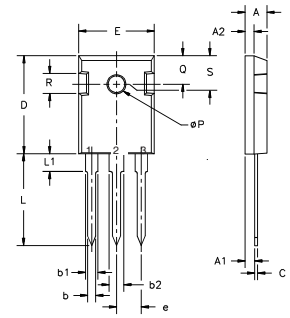
### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions (T <sub>J</sub> = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>CES</sub>	I <sub>C</sub> = 250μA, V <sub>GE</sub> = 0V	600		V
V <sub>GE(th)</sub>	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>	3.0		V
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> V <sub>GE</sub> = 0V      T <sub>J</sub> = 125°C			75 μA 750 μA
I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ± 20V			±100 nA
V <sub>CE(sat)</sub>	I <sub>C</sub> = 60A, V <sub>GE</sub> = 15V, Note 1			1.35 V

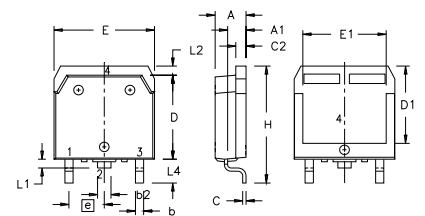
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60A, V_{CE} = 10V$ , Note 1	48	76	S
$C_{ies}$	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		6600	pF
$C_{oes}$			360	pF
$C_{res}$			80	pF
$Q_g$	$I_C = I_{C110}, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		230	nC
$Q_{ge}$			40	nC
$Q_{gc}$			78	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ C</math></b> $I_C = 50A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 3\Omega$		31	ns
$t_{ri}$			34	ns
$E_{on}$			1.38	mJ
$t_{d(off)}$			320	ns
$t_{fi}$			250	ns
$E_{off}$			3.5	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ C</math></b> $I_C = 50A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 3\Omega$		29	ns
$t_{ri}$			32	ns
$E_{on}$			2.6	mJ
$t_{d(off)}$			510	ns
$t_{fi}$			375	ns
$E_{off}$			6.5	mJ
$R_{thJC}$			0.23	$^\circ C/W$
$R_{thCS}$		0.15		$^\circ C/W$

Note 1: Pulse test,  $t \leq 300\mu s$ , duty cycle,  $d \leq 2\%$ .

**TO-247 AD Outline**


Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

**TO-268 Outline**


Terminals: 1 - Gate 2 - Drain

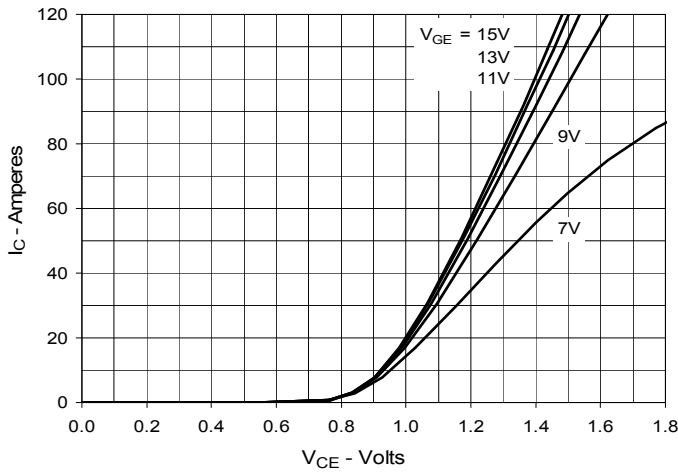
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions and dimensions.

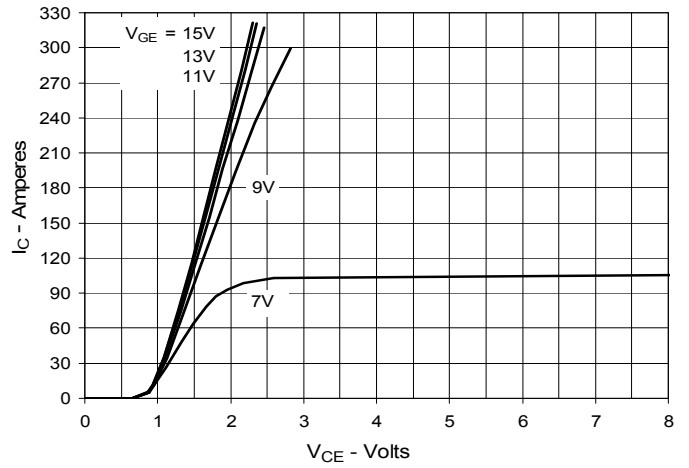
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

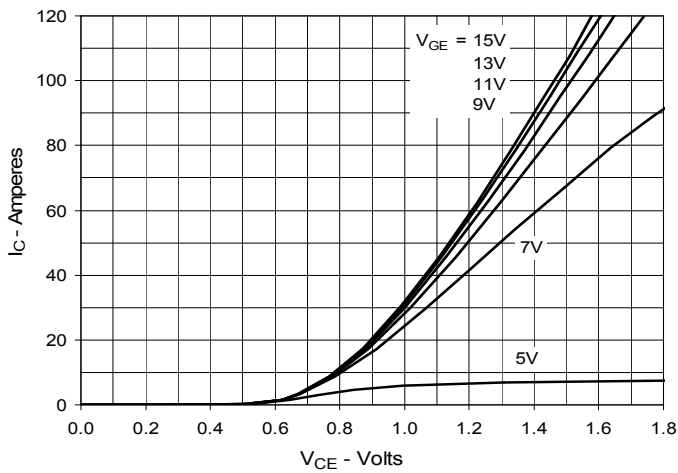
**Fig. 1. Output Characteristics @ 25°C**



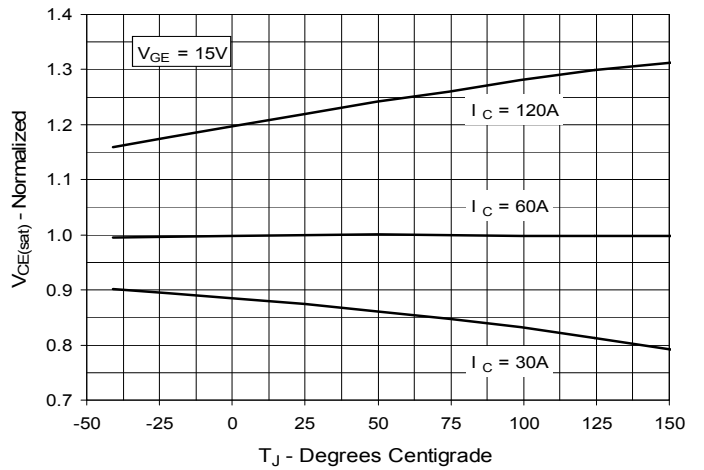
**Fig. 2. Extended Output Characteristics @ 25°C**



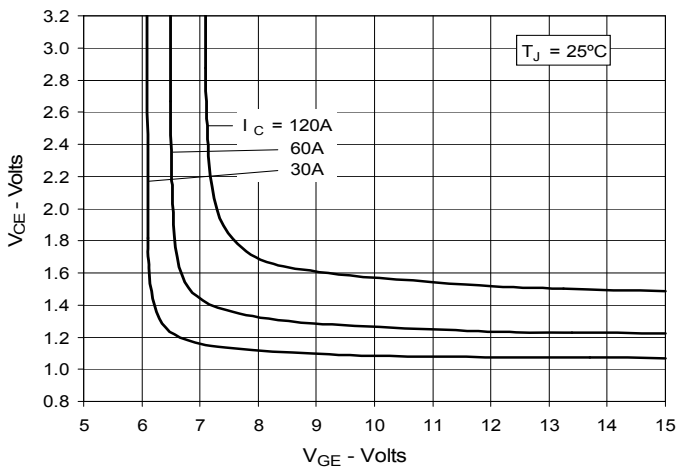
**Fig. 3. Output Characteristics @ 125°C**



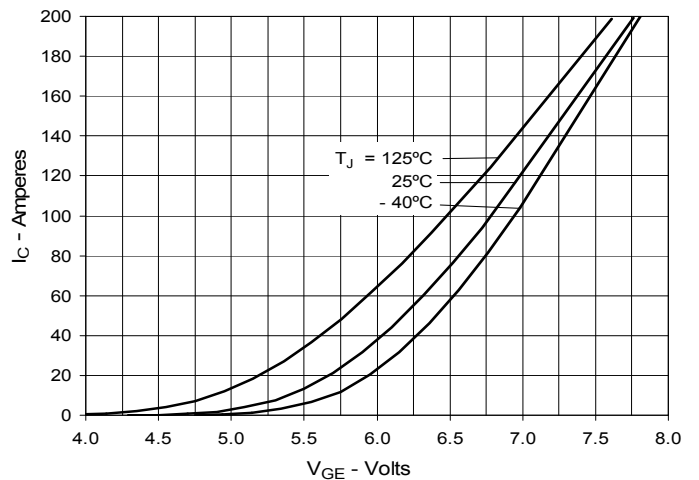
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



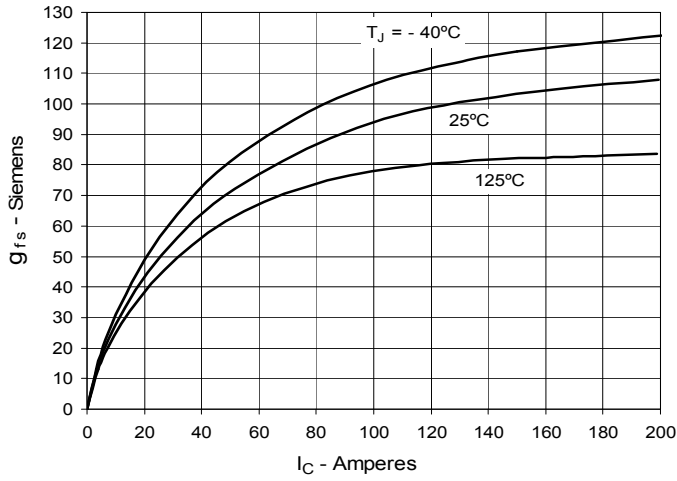
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



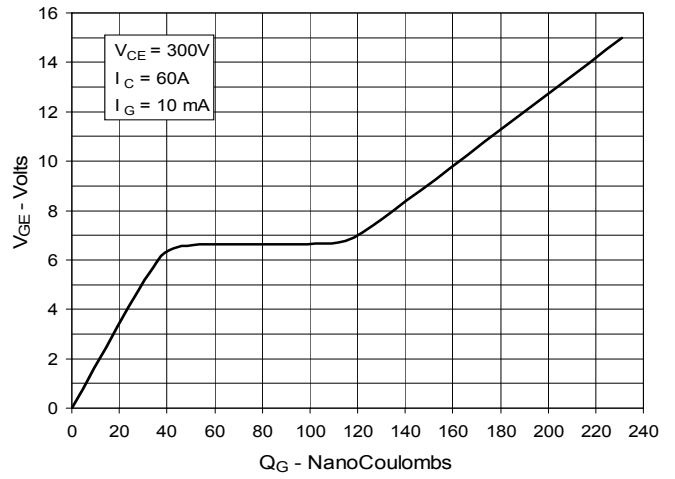
**Fig. 6. Input Admittance**



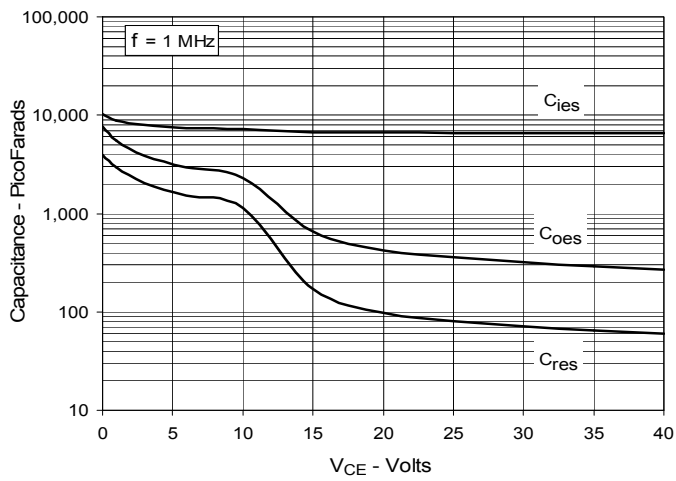
**Fig. 7. Transconductance**



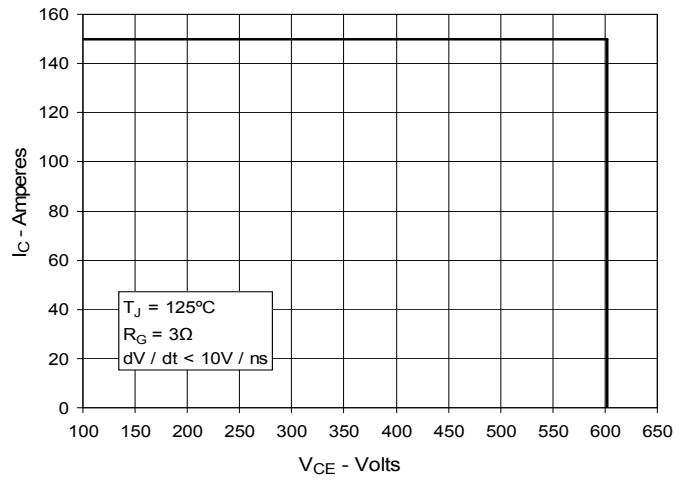
**Fig. 8. Gate Charge**



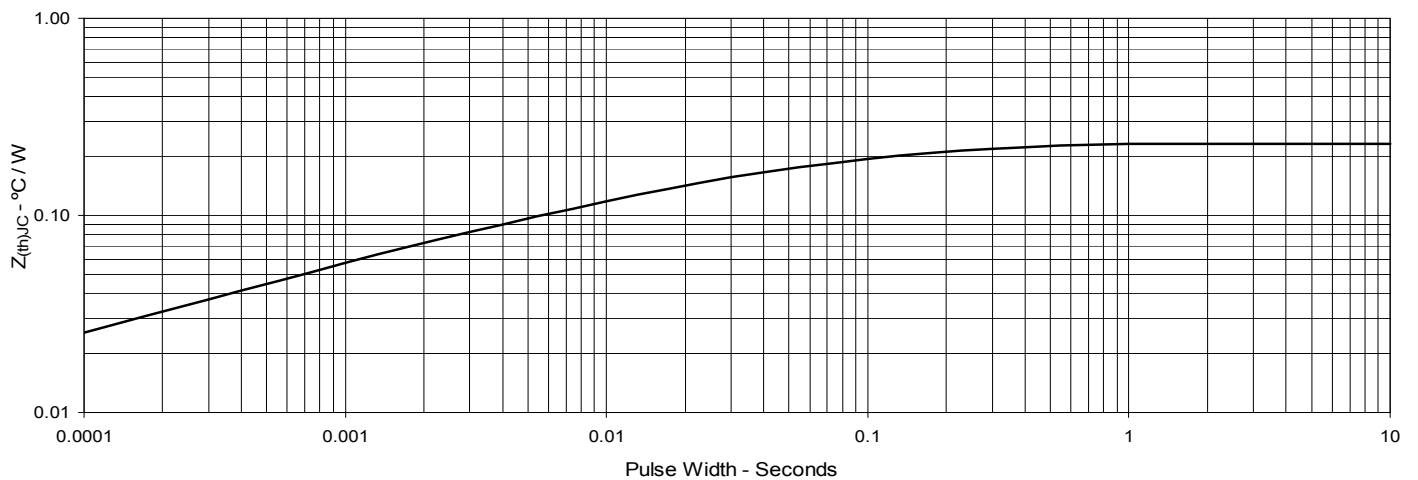
**Fig. 9. Capacitance**



**Fig. 10. Reverse-Bias Safe Operating Area**

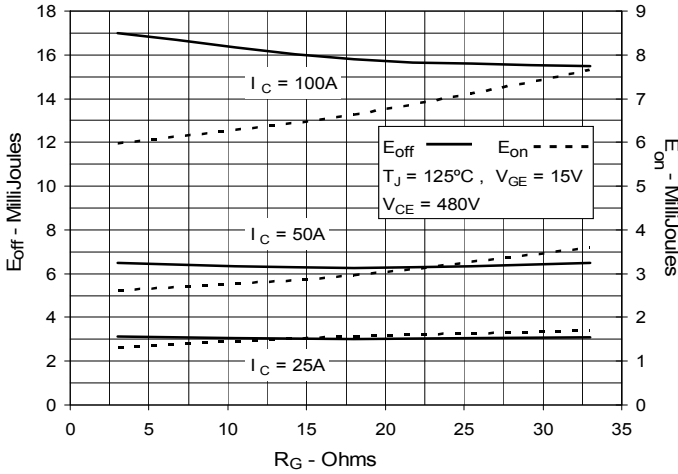


**Fig. 11. Maximum Transient Thermal Impedance**

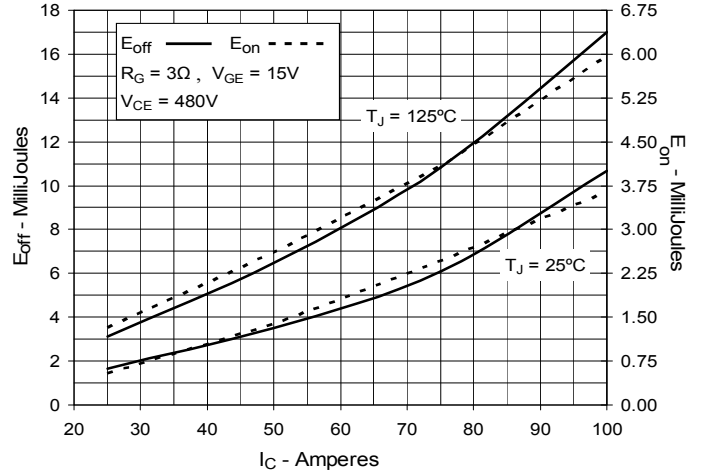


IXYS reserves the right to change limits, test conditions and dimensions.

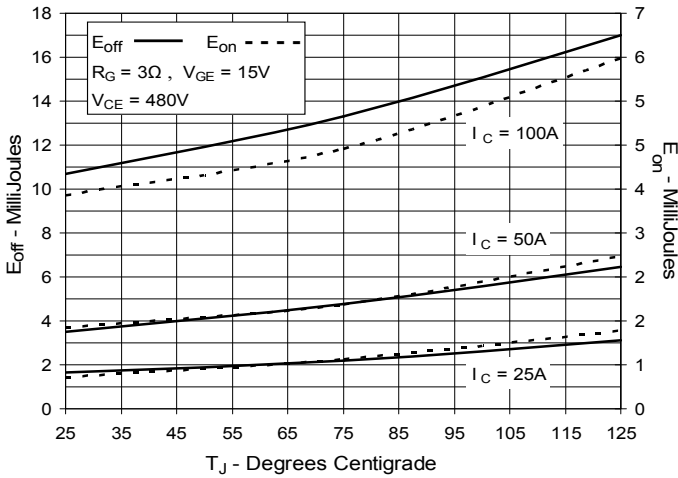
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



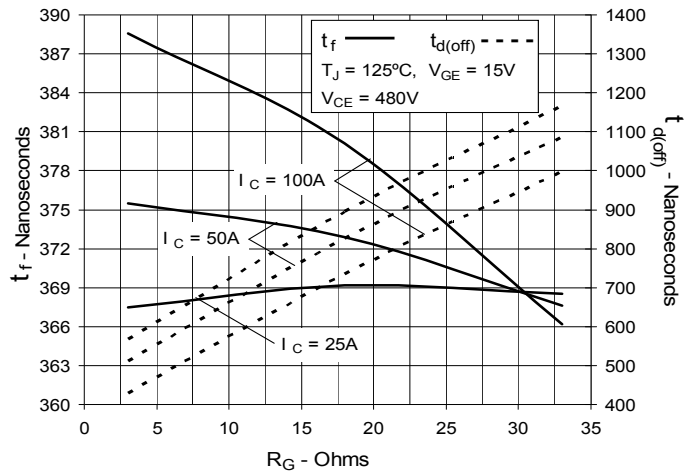
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



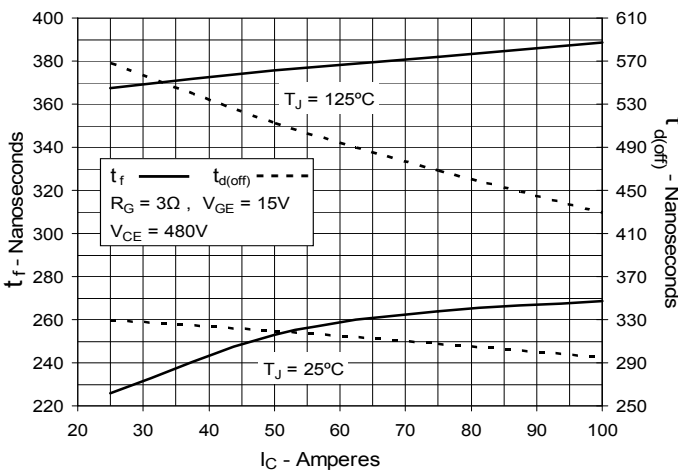
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



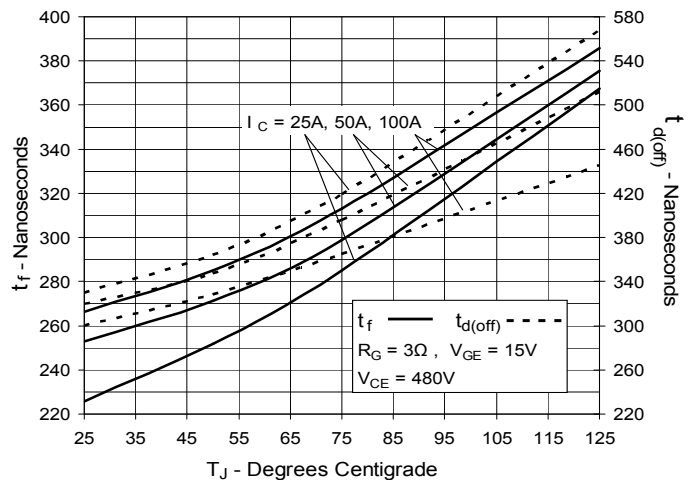
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



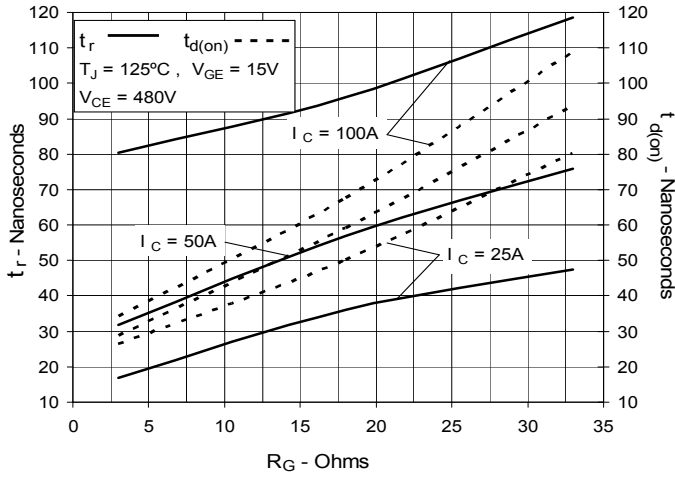
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



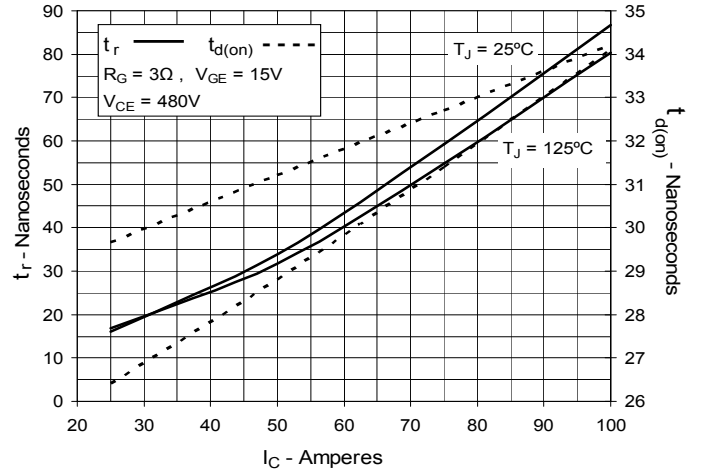
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

